OPB817Z



Features:

- 0.20" (5.08 mm) wide gap, 0.86" (21.84 mm) deep slot
- 24" (609 mm) 26 AWG wires
- Dust protection
- Two mounting tabs



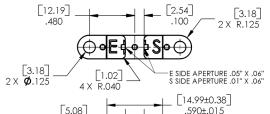
Description:

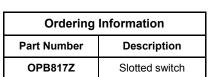
The OPB817Z slotted switch consists of an infrared emitting diode and a NPN silicon phototransistor mounted in an opaque housing with clear windows for dust protection. Switching of the phototransistor occurs whenever an opaque object passes through the slot.

The OPB817Z has an 0.86" (21.844 mm) deep slot allowing for a longer reach of the optical center line from the mounting plane. The phototransistor internal apertures are 0.10" x 0.06" (0.25 mm x 1.52 mm) on the sensor side ("S") and 0.05" x 0.06" (1.27 mm x 1.52 mm) on the emitter side ("E").

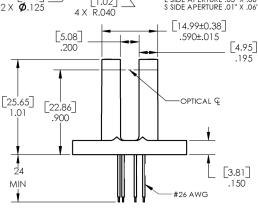
Applications:

- Non-contact object sensing
- Assembly line automation
- Machine automation
- Equipment security
- Machine safety







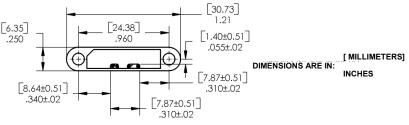


Wire Color	Description				
Red	Anode				
Black	Cathode				
White	Collector				
Green	Emitter				

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RoHS



General Note





Electrical Specifications

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Storage & Operating Temperature Range	-40° C to +85° C
Lead Soldering Temperature [1/16 inch (1.6mm) from the case for 5 sec. with soldering iron] (1)	260° C

Input Diode

Part State	
Forward DC Current	50 mA
Peak Forward Current (1 μs pulse width, 300 pps)	3 A
Reverse DC Voltage	2 V
Power Dissipation ⁽²⁾	100 mW

Output Phototransistor

Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Collector DC Current	30 mA
Power Dissipation ⁽²⁾	100 mW

Electrical Characteristics (T_A = 25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS	
Input Diode (see OP140 for additional information)							
V_{F}	Forward Voltage	-	-	1.8	٧	I _F = 20 mA	
I _R	Reverse Current	-	-	100	μΑ	V _R = 2 V	
Output Phototransistor (see OP552 for additional information)							

Output Phototransistor (see OP552 for additional information)

$V_{(BR)(CEO)}$	Collector-Emitter Breakdown Voltage	30	-	-	٧	$I_C = 1 \text{ mA}, I_F = 0, E_E = 0$
V _{(BR)(ECO)}	Emitter-Collector Breakdown Voltage	5	-	1	٧	$I_E = 100 \mu A, I_F = 0, E_E = 0$
I _{CEO}	Collector-Emitter Leakage Current	-	-	100	nA	$V_{CE} = 10 \text{ V}, I_F = 0, E_E = 0$

Coupled

I _{C(ON)}	On-State Collector Current	1.0	-	10.0	mA	V _{CE} = 5 V, I _F = 20 mA
V _{CE(SAT)}	Collector-Emitter	-	1	0.4	٧	I _C = 100 μA, I _F = 20 mA

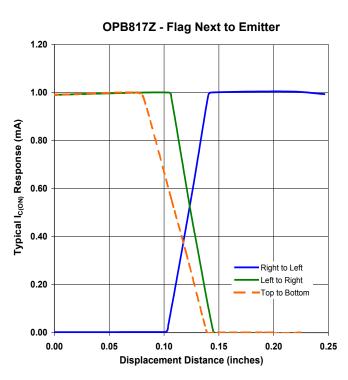
Notes:

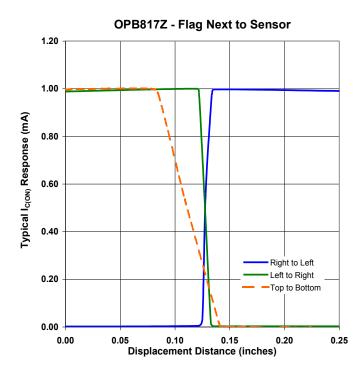
- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- Derate linearly 1.67 mW/°C above 25° C. (2)
- All parameters were tested using pulse techniques.
- Lead spacing of 0.220" (5.59 mm) or 0.320" (8.13 mm) is available. Leads are 0.20" square (5.08 mm) and 0.425" long (10.80 mm), which is (4) the minimum.
- Methanol or isopropanol are recommended as cleaning agents. Plastic housing is soluble in chlorinated hydrocarbons and ketones. Spray and wipe; do not submerge.
- Polarity is denoted by color of housing top: LED (gray or clear), sensor (black).
- Clear dust protection.

OPB817Z

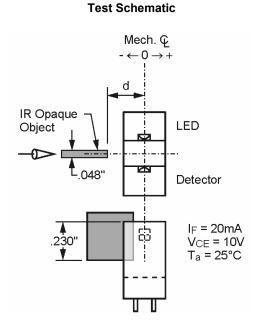


Performance





OPB817Z - Flag in Middle of Slot 1.20 1.00 Typical I_{C(ON)} Response (mA) 0.80 0.60 0.40 Right to Left Left to Right 0.20 Top to Bottom 0.00 0.05 0.10 0.00 0.15 0.20 0.25 **Displacement Distance (inches)**



General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.





Issue	Change Description	Approval	Date
A	Initial Release		
A.1	Revised and put into new format. Required changes on all pages.		11/28/05
A.2	Changed soldering temp to 260° C and changed footer's issue number		01/11/06
	and date.		